Andreas Klein

List of Publications by Year
in descending order

273	10,723	31902	48187
papers	citations	53 h-index	88 g-index

282	282	282	11901
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Nature of the Band Gap of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>In</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:math>Revealed by First-Principles Calculations and X-Ray Spectroscopy. Physical Review Letters, 2008, 100, 167402.	2.9	576
2	First-principles study of intrinsic point defects in ZnO: Role of band structure, volume relaxation, and finite-size effects. Physical Review B, 2006, 73, .	1.1	463
3	Transparent Conducting Oxides for Photovoltaics: Manipulation of Fermi Level, Work Function and Energy Band Alignment. Materials, 2010, 3, 4892-4914.	1.3	360
4	Energy Band Alignment between Anatase and Rutile TiO₂. Journal of Physical Chemistry Letters, 2013, 4, 4182-4187.	2.1	210
5	Enhanced specific grain boundary conductivity in nanocrystalline Y2O3-stabilized zirconia. Solid State Ionics, 1999, 118, 331-339.	1.3	192
6	Band structure of indium oxide: Indirect versus direct band gap. Physical Review B, 2007, 75, .	1.1	180
7	Surface states, surface potentials, and segregation at surfaces of tin-dopedIn2O3. Physical Review B, 2006, 73, .	1.1	175
8	Electronic band structure of single-crystal and single-layerWS2:Influence of interlayer van der Waals interactions. Physical Review B, 2001, 64, .	1.1	165
9	First-principles study of the structure and stability of oxygen defects in zinc oxide. Physical Review B, 2005, 72, .	1.1	165
10	Interface properties and band alignment of Cu2S/CdS thin film solar cells. Thin Solid Films, 2003, 431-432, 477-482.	0.8	160
11	The Work Function of TiO2. Surfaces, 2018, 1, 73-89.	1.0	157
12	Preparation of RuO₂/TiO₂ Mesoporous Heterostructures and Rationalization of Their Enhanced Photocatalytic Properties by Band Alignment Investigations. Journal of Physical Chemistry C, 2013, 117, 22098-22110.	1.5	155
13	Electronic properties of In2O3 surfaces. Applied Physics Letters, 2000, 77, 2009-2011.	1.5	143
14	Surface potentials of magnetron sputtered transparent conducting oxides. Thin Solid Films, 2009, 518, 1197-1203.	0.8	136
15	Energy band alignment at interfaces of semiconducting oxides: A review of experimental determination using photoelectron spectroscopy and comparison with theoretical predictions by the electron affinity rule, charge neutrality levels, and the common anion rule. Thin Solid Films, 2012, 520, 3721-3728.	0.8	128
16	Surface versus bulk electronic/defect structures of transparent conducting oxides: I. Indium oxide and ITO. Journal Physics D: Applied Physics, 2006, 39, 3959-3968.	1.3	126
17	Barrier height at<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mrow><mml:mo>(</mml:mo><mml:mrow><mml:mtext>Ba</mml:mtext><mml:mo>,</mml:mo> studied by photoemission. Physical Review B, 2008, 77, .	1.1	125
18	Transparent Conducting Oxides: Electronic Structureâ€“Property Relationship from Photoelectron Spectroscopy with in situ Sample Preparation. Journal of the American Ceramic Society, 2013, 96, 331-345.	1.9	123

#	Article	IF	Citations
19	Electronic structure of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>In</mml:mtext></mml:mrow><mml:mn>2</mml:mn></mml:msub> Sn-doped<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>In</mml:mtext></mml:mrow><mml:mn>2</mml:mn></mml:msub> Physical Review B, 2010, 81, .	1.1	114
20	Interface Engineering of Inorganic Thinâ€Film Solar Cells â€“ Materialsâ€Science Challenges for Advanced Physical Concepts. Advanced Materials, 2009, 21, 4196-4206.	11.1	113
21	Efficiency limitations of thermally evaporated thin-film SnS solar cells. Journal Physics D: Applied Physics, 2013, 46, 305109.	1.3	112
22	Electronic and Chemical Properties of Tin-Doped Indium Oxide (ITO) Surfaces and ITO/ZnPc Interfaces Studied In-situ by Photoelectron Spectroscopy. Journal of Physical Chemistry B, 2006, 110, 4793-4801.	1.2	108
23	Band Alignment Engineering at Cu₂O/ZnO Heterointerfaces. ACS Applied Materials & Interfaces, 2016, 8, 21824-21831.	4.0	101
24	Limitation of Fermi level shifts by polaron defect states in hematite photoelectrodes. Nature Communications, 2018, 9, 4309.	5.8	95
25	Energy band alignment in chalcogenide thin film solar cells from photoelectron spectroscopy. Journal of Physics Condensed Matter, 2015, 27, 134201.	0.7	92
26	Optimized chemical bath deposited CdS layers for the improvement of CdTe solar cells. Solar Energy Materials and Solar Cells, 2011, 95, 816-820.	3.0	91
27	Fermi-level-dependent defect formation in Cu-chalcopyrite semiconductors. Applied Physics Letters, 1999, 74, 2283-2285.	1.5	88
28	Reactive magnetron sputtering of Cu2O: Dependence on oxygen pressure and interface formation with indium tin oxide. Journal of Applied Physics, 2011, 109, .	1.1	87
29	Thin film growth and band lineup of In2O3 on the layered semiconductor InSe. Journal of Applied Physics, 1999, 86, 5687-5691.	1.1	86
30	Efficacy of the DFTÂ+Â <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>U</mml:mi></mml:math> formalism for modeling hole polarons in perovskite oxides. Physical Review B, 2014, 90, .	1.1	86
31	Band energy diagram of CdTe thin film solar cells. Thin Solid Films, 2002, 403-404, 252-257.	0.8	83
32	Thin Film Solar Cells: Materials Science at Interfaces. Advanced Engineering Materials, 2005, 7, 914-920.	1.6	74
33	Polarization dependence of Schottky barrier heights at interfaces of ferroelectrics determined by photoelectron spectroscopy. Physical Review B, 2012, 86, .	1.1	74
34	Improved photocatalytic activity in RuO₂â€“ZnO nanoparticulate heterostructures due to inhomogeneous space charge effects. Physical Chemistry Chemical Physics, 2015, 17, 5090-5102.	1.3	73
35	Defect chemistry and resistance degradation in Fe-doped SrTiO3 single crystal. Acta Materialia, 2016, 108, 229-240.	3.8	73
36	Geometry, electronic structure and thermodynamic stability of intrinsic point defects in indium oxide. Journal of Physics Condensed Matter, 2009, 21, 455801.	0.7	71

#	Article	IF	Citations
37	Interface Properties of Dielectric Oxides. Journal of the American Ceramic Society, 2016, 99, 369-387.	1.9	70
38	CdTe thin film solar cells: Interrelation of nucleation, structure, and performance. Thin Solid Films, 2009, 517, 2125-2131.	0.8	68
39	Band lineup of lattice mismatched InSe/GaSe quantum well structures prepared by van der Waals epitaxy: Absence of interfacial dipoles. Journal of Applied Physics, 1996, 80, 3817-3821.	1.1	67
40	Influence of Mg content on the band alignment at CdSâˆ•(Zn,Mg)O interfaces. Applied Physics Letters, 2005, 87, 032101.	1.5	63
41	Studies of sputtered ZnTe films as interlayer for the CdTe thin film solar cell. Thin Solid Films, 2005, 480-481, 204-207.	0.8	62
42	Intrinsic energy band alignment of functional oxides. Physica Status Solidi - Rapid Research Letters, 2014, 8, 571-576.	1.2	60
43	[illegible]<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow /><mml:mrow><mml:mn>3</mml:mn></mml:mrow></mml:msub></mml:mrow></mml:math>/SrTiO<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow /><mml:mrow><mml:mn>3</mml:mn></mml:mrow></mml:msub></mml:mrow></mml:math> interface: Ex	1.1	59
44	In-Situ Preparation and Analysis of Functional Oxides. Advanced Engineering Materials, 2005, 7, 945-949.	1.6	58
45	Non-stoichiometry and electronic properties of interfaces. Journal of Materials Science, 2007, 42, 1890-1900.	1.7	58
46	Limits for n-type doping in In2O3 and SnO2: A theoretical approach by first-principles calculations using hybrid-functional methodology. Journal of Applied Physics, 2010, 108, .	1.1	57
47	Analysis of the interfacial characteristics of BiVO₄/metal oxide heterostructures and its implication on their junction properties. Physical Chemistry Chemical Physics, 2019, 21, 5086-5096.	1.3	56
48	Laterally inhomogeneous surface-potential distribution and photovoltage at clustered In/WSe2(0001) interfaces. Physical Review B, 1993, 48, 14242-14252.	1.1	55
49	Density-functional-theory calculations of electronic band structure of single-crystal and single-layerWS2. Physical Review B, 2002, 66, .	1.1	55
50	Changes in Electronic Structure and Chemical Bonding upon Crystallization of the Phase Change Material<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>GeSb</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi>Te</mml:mi><mml:mi><mml: Physical Review Letters, 2008, 100, 016402.	2.9	55
51	Barrier heights at the SnO2/Pt interface: In situ photoemission and electrical properties. Surface Science, 2008, 602, 3246-3252.	0.8	54
52	Surface and bulk properties of sputter deposited undoped and Sb-doped SnO2 thin films. Sensors and Actuators B: Chemical, 2009, 139, 665-672.	4.0	54
53	Band lineup between CdS and ultra high vacuum-cleaved CuInS2 single crystals. Applied Physics Letters, 1997, 70, 1299-1301.	1.5	53
54	Influence of orbital contributions to the valence band alignment of Bi<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>O<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>3</mml:mn></mml:msub></mml:math>, Fe<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:	1.1	53

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55	Electronic surface properties of rf-magnetron sputtered InO:Sn. Solid State Ionics, 2004, 173, 141-145.	1.3	52
56	Surface analysis of CdTe thin film solar cells. Thin Solid Films, 2001, 387, 161-164.	0.8	51
57	12% efficient CdTe/CdS thin film solar cells deposited by low-temperature close space sublimation. Journal of Applied Physics, 2011, 110, .	1.1	51
58	Design of Lead-Free Antiferroelectric (1 â€“ x)NaNbO₃â€“xSrSnO₃ Compositions Guided by First-Principles Calculations. Chemistry of Materials, 2021, 33, 266-274.	3.2	50
59	Electronic properties and interface characterization of phthalocyanine and Ru-polypyridine dyes on TiO2 surface. Surface Science, 2003, 539, 37-48.	0.8	49
60	In Situ Hall Effect Monitoring of Vacuum Annealing of In2O3:H Thin Films. Materials, 2015, 8, 561-574.	1.3	48
61	Photoemission study and band alignment of the CuInSe2(001)/CdS heterojunction. Applied Physics Letters, 2004, 84, 3067-3069.	1.5	47
62	Energy band alignment between Pb(Zr,Ti)O₃ and high and low work function conducting oxidesâ€”from hole to electron injection. Journal Physics D: Applied Physics, 2010, 43, 295301.	1.3	47
63	Characterization of tellurium layers for back contact formation on close to technology treated CdTe surfaces. Journal of Applied Physics, 2003, 94, 3589-3598.	1.1	44
64	Growth regimes of CdTe deposited by close-spaced sublimation for application in thin film solar cells. Thin Solid Films, 2007, 515, 5814-5818.	0.8	44
65	Interface Investigation in Nanostructured BaTiO₃/Silica Composite Ceramics. Journal of the American Ceramic Society, 2010, 93, 865-874.	1.9	44
66	Surface energy controlled preferential orientation of thin films. Journal Physics D: Applied Physics, 2010, 43, 055301.	1.3	43
67	Influence of the PVD sputtering method on structural characteristics of SiCN-coatings â€” Comparison of RF, DC and HiPIMS sputtering and target configurations. Surface and Coatings Technology, 2011, 205, S119-S123.	2.2	43
68	Reduction-induced Fermi level pinning at the interfaces between Pb(Zr,Ti)O₃ and Pt, Cu and Ag metal electrodes. Journal Physics D: Applied Physics, 2011, 44, 255301.	1.3	43
69	Reactively magnetron sputtered Bi₂<scp>O</scp>₃ thin films: Analysis of structure, optoelectronic, interface, and photovoltaic properties. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 93-100.	0.8	43
70	Influence of Cu(In,Ga)Se2 band gap on the valence band offset with CdS. Thin Solid Films, 2004, 451-452, 420-423.	0.8	42
71	Electronic structure of In2O3 from resonant x-ray emission spectroscopy. Applied Physics Letters, 2009, 94, .	1.5	42
72	Utilization of sputter depth profiling for the determination of band alignment at polycrystalline CdTe/CdS heterointerfaces. Applied Physics Letters, 2002, 81, 2297-2299.	1.5	41

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73	Chemical interaction of Na with cleaved (011) surfaces of CuInSe2. Journal of Applied Physics, 1996, 80, 5039-5043.	1.1	40
74	In situ preparation and interface characterization of TiO2/Cu2S heterointerface. Applied Physics Letters, 2003, 82, 2269-2271.	1.5	40
75	Nanoscaled tin dioxide films processed from organotin-based hybrid materials: an organometallic route toward metal oxide gas sensors. Nanoscale, 2012, 4, 6806.	2.8	40
76	Influence of dopant species and concentration on grain boundary scattering in degenerately doped In2O3 thin films. Thin Solid Films, 2016, 614, 62-68.	0.8	40
77	Chemical and electronic properties of the ITO/Al2O3 interface. Physical Chemistry Chemical Physics, 2009, 11, 3049.	1.3	39
78	Barrier heights, polarization switching, and electrical fatigue in Pb(Zr,Ti)O3 ceramics with different electrodes. Journal of Applied Physics, 2010, 108, .	1.1	39
79	A photoemission study of barrier and transport properties of the interfaces of Au and Cu with WSe2(0001) surfaces. Surface Science, 1994, 321, 19-31.	0.8	38
80	Energy-Band Alignment of BiVO₄ from Photoelectron Spectroscopy of Solid-State Interfaces. Journal of Physical Chemistry C, 2018, 122, 20861-20870.	1.5	38
81	Pinning of the Fermi Level in CuFeO₂ by Polaron Formation Limiting the Photovoltage for Photochemical Water Splitting. Advanced Functional Materials, 2020, 30, 1910432.	7.8	38
82	Interface modification of CdTe thin film solar cells by CdCl2-activation. Thin Solid Films, 2003, 431-432, 267-271.	0.8	37
83	In situ photoelectron study of the (Ba,Sr)TiO3/RuO2 contact formation. Journal of the European Ceramic Society, 2010, 30, 187-192.	2.8	37
84	Self-Assembled Nanowire Networks by Deposition of Copper onto Layered-Crystal Surfaces. Advanced Materials, 2002, 14, 1056.	11.1	36
85	Properties of sputtered ZnO films and its interfaces with CdS. Thin Solid Films, 2003, 431-432, 378-381.	0.8	36
86	Formation and modification of Schottky barriers at the PZT/Pt interface. Journal Physics D: Applied Physics, 2009, 42, 215302.	1.3	36
87	CdTe thin film solar cells with reduced CdS film thickness. Thin Solid Films, 2011, 519, 7138-7141.	0.8	36
88	Orientation dependent ionization potential of In₂O₃: a natural source for inhomogeneous barrier formation at electrode interfaces in organic electronics. Journal of Physics Condensed Matter, 2011, 23, 334203.	0.7	36
89	Atomic Layer Deposition of Al₂O₃ onto Sn-Doped In₂O₃: Absence of Self-Limited Adsorption during Initial Growth by Oxygen Diffusion from the Substrate and Band Offset Modification by Fermi Level Pinning in Al₂O₃. Chemistry of Materials, 2012, 24, 4503-4510.	3.2	36
90	Photovoltaic properties of WSe2 single-crystals studied by photoelectron spectroscopy. Solar Energy Materials and Solar Cells, 1998, 51, 181-191.	3.0	34

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91	Effect of in situ UHV CdCl2-activation on the electronic properties of CdTe thin film solar cells. Thin Solid Films, 2003, 431-432, 84-89.	0.8	34
92	Investigations on RF-magnetron sputtered Co₃O₄thin films regarding the solar energy conversion properties. Journal Physics D: Applied Physics, 2016, 49, 155306.	1.3	34
93	Influence of material synthesis and doping on the transport properties of WSe2 single crystals grown by selenium transport. Solar Energy Materials and Solar Cells, 1997, 46, 175-186.	3.0	33
94	Surface science studies of Cu containing back contacts for CdTe solar cells. Thin Solid Films, 2007, 515, 6172-6174.	0.8	33
95	ZnO and Its Applications. Springer Series in Materials Science, 2008, , 1-33.	0.4	33
96	Deposition and characterization of highly p-type antimony doped ZnTe thin films. Thin Solid Films, 2009, 517, 2149-2152.	0.8	33
97	Electrocatalytic Properties of (100)-, (110)-, and (111)-Oriented NiO Thin Films toward the Oxygen Evolution Reaction. Journal of Physical Chemistry C, 2018, 122, 22252-22263.	1.5	33
98	Water adsorption on UHV cleaved InP(110) surfaces. Surface Science, 2000, 457, L337-L341.	0.8	32
99	Domain wall stability in ferroelectrics with space charges. Journal of Applied Physics, 2014, 115, .	1.1	32
100	Fermi Level Positions and Induced Band Bending at Single Crystalline Anatase (101) and (001) Surfaces: Origin of the Enhanced Photocatalytic Activity of Facet Engineered Crystals. Advanced Energy Materials, 2018, 8, 1802195.	10.2	32
101	Electronically Decoupled Films of InSe Prepared by van der Waals Epitaxy: Localized and Delocalized Valence States. Physical Review Letters, 1998, 80, 361-364.	2.9	31
102	XPS analysis of wet chemical etching of GaAs(110) by Br2â€“H2O: comparison of emersion and model experiments. Electrochimica Acta, 2000, 45, 4663-4672.	2.6	31
103	Structural dipoles at interfaces between polar II-VI semiconductors CdS and CdTe and non-polar layered transition metal dichalcogenide semiconductors MoTe2and WSe2. Semiconductor Science and Technology, 2000, 15, 514-522.	1.0	31
104	Band offset at the CuGaSe2âˆ•In2S3 heterointerface. Applied Physics Letters, 2004, 85, 961-963.	1.5	31
105	An optimized multilayer structure of CdS layer for CdTe solar cells application. Journal of Alloys and Compounds, 2011, 509, 5285-5289.	2.8	31
106	Comparison between the structural, morphological and optical properties of CdS layers prepared by Close Space Sublimation and RF magnetron sputtering for CdTe solar cells. Thin Solid Films, 2011, 519, 7596-7599.	0.8	31
107	Highly oriented layers of the threeâ€dimensional semiconductor CdTe on the twoâ€dimensional layered semiconductors MoTe2and WSe2. Journal of Applied Physics, 1996, 80, 5718-5722.	1.1	30
108	Nitrogen doping of ZnTe and its influence on CdTeâˆ•ZnTe interfaces. Applied Physics Letters, 2007, 90, 062112.	1.5	30

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109	Properties of SiCN coatings for high temperature applications â€" Comparison of RF-, DC- and HPPMS-sputtering. Surface and Coatings Technology, 2010, 205, S21-S27.	2.2	30
110	Influence of substrate temperature, growth rate and TCO substrate on the properties of CSS deposited CdS thin films. Thin Solid Films, 2011, 519, 7556-7559.	0.8	30
111	Surface potentials of (111), (110) and (100) oriented CeO 2â^'x thin films. Applied Surface Science, 2016, 377, 1-8.	3.1	30
112	Fermi level-dependent defect formation at Cu(In,Ga)Se2 interfaces. Applied Surface Science, 2000, 166, 508-512.	3.1	29
113	Oriented growth and band alignment at the CdTe/CdS interface. Thin Solid Films, 2001, 387, 158-160.	0.8	29
114	Carrier Generation and Inherent Off-Stoichiometry in Zn, Sn Codoped Indium Oxide (ZITO) Bulk and Thin-Film Specimens. Journal of the American Ceramic Society, 2008, 91, 467-472.	1.9	29
115	Influence of sputter deposition parameters on the properties of tunable barium strontium titanate thin films for microwave applications. Journal of the European Ceramic Society, 2009, 29, 1433-1442.	2.8	29
116	Sputter-deposited polycrystalline tantalum-doped SnO2 layers. Thin Solid Films, 2014, 555, 173-178.	0.8	29
117	Influence of grain boundaries and interfaces on the electronic structure of polycrystalline CuO thin films. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1615-1624.	0.8	29
118	Quasi van der Waals epitaxy of ZnSe on the layered chalcogenides InSe and GaSe. Thin Solid Films, 2000, 380, 263-265.	0.8	28
119	Band offsets at the ZnSe/CuGaSe2(001) heterointerface. Applied Physics Letters, 1999, 74, 1099-1101.	1.5	27
120	Electronic properties of WS2 monolayer films. Thin Solid Films, 2000, 380, 221-223.	0.8	27
121	PVD of copper sulfide (Cu2S) for PIN-structured solar cells. Journal Physics D: Applied Physics, 2013, 46, 495112.	1.3	27
122	A Spaceâ€€Charge Treatment of the Increased Concentration of Reactive Species at the Surface of a Ceria Solid Solution. Angewandte Chemie - International Edition, 2017, 56, 14516-14520.	7.2	27
123	H2O adsorption on the layered chalcogenide semiconductors WSe2, InSe and GaSe. Surface Science, 1992, 269-270, 909-914.	0.8	26
124	Band alignment of differently treated TCO/CdS interface. Thin Solid Films, 2009, 517, 2558-2561.	0.8	26
125	A possible way to reduce absorber layer thickness in thin film CdTe solar cells. Thin Solid Films, 2013, 535, 233-236.	0.8	26
126	Nickel Oxide Selectively Deposited on the {101} Facet of Anatase TiO₂ Nanocrystal Bipyramids for Enhanced Photocatalysis. ACS Applied Nano Materials, 2019, 2, 4793-4803.	2.4	26

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127	The In2O3/CdTe interface: A possible contact for thin film solar cells?. Applied Physics A: Materials Science and Processing, 2006, 82, 281-285.	1.1	25
128	Annealing effects on the chemical deposited CdS films and the electrical properties of CdS/CdTe solar cells. Materials Research Bulletin, 2011, 46, 194-198.	2.7	25
129	Role of copper interstitials in CuInSe<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>: First-principles calculations. Physical Review B, 2011, 84, .	1.1	25
130	SnO2 Films Deposited by Ultrasonic Spray Pyrolysis: Influence of Al Incorporation on the Properties. Molecules, 2019, 24, 2797.	1.7	25
131	Low temperature adsorption of water on cleaved GaAs(110) surfaces. Surface Science, 1996, 366, L685-L688.	0.8	24
132	Chemical character of BC_xN_y layers grown by CVD with trimethylamine borane. X-Ray Spectrometry, 2009, 38, 68-73.	0.9	24
133	Electrical properties of (Ba, Sr)TiO3thin films with Pt and ITO electrodes: dielectric and rectifying behaviour. Journal of Physics Condensed Matter, 2011, 23, 334202.	0.7	24
134	Growth and surface properties of epitaxial SnO₂. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 1997-2004.	0.8	24
135	Study of electrical fatigue by defect engineering in organic light-emitting diodes. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2015, 192, 26-51.	1.7	24
136	Perspectives of the concept of van der Waals epitaxy: growth of lattice mismatched GaSe(0001) films on Si(111), Si(110) and Si(100). Thin Solid Films, 2000, 380, 276-281.	0.8	23
137	Alternative back contacts for CdTe solar cells: a photoemission study of the VSe2/CdTe and TiSe2/CdTe interface formation. Thin Solid Films, 2003, 431-432, 382-386.	0.8	23
138	Copper (I) Oxide (Cu₂O) based back contact for pâ€iâ€n CdTe solar cells. Progress in Photovoltaics: Research and Applications, 2016, 24, 1229-1236.	4.4	23
139	Polarisation dependence of Schottky barrier heights at ferroelectric BaTiO₃â€‰/â€‰RuO₂interfaces: influence of substrate orientation and quality. Journal Physics D: Applied Physics, 2016, 49, 295304.	1.3	23
140	Defect Modulation Doping. Advanced Functional Materials, 2019, 29, 1807906.	7.8	23
141	Partial density of states in the CuInSe2â€‰ valence bands. Journal of Applied Physics, 1997, 81, 7806-7809.	1.1	22
142	Surface potential changes of semiconducting oxides monitored by high-pressure photoelectron spectroscopy: Importance of electron concentration at the surface. Solid State Ionics, 2006, 177, 3123-3127.	1.3	22
143	Junction formation of CuInSe2 with CdS: A comparative study of â€œdryâ€•and â€œwetâ€•interfaces. Thin Solid Films, 2007, 515, 6112-6118.	0.8	22
144	Multi-Level Cell Properties of a Bilayer Cu2O/Al2O3 Resistive Switching Device. Nanomaterials, 2019, 9, 289.	1.9	22

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145	An option for the surface science on Cu chalcopyrites: the selenium capping and decapping process. Surface Science, 2004, 557, 263-268.	0.8	21
146	In situ photoemission study of the contact formation of (Ba,Sr)TiO3 with Cu and Au. Solid State Ionics, 2006, 177, 1659-1664.	1.3	21
147	Piezotronic effect at Schottky barrier of a metal-ZnO single crystal interface. Journal of Applied Physics, 2017, 121, 155701.	1.1	21
148	Chemical passivation of Si(111) capped by a thin GaSe layer. Applied Surface Science, 2000, 167, 122-124.	3.1	20
149	Electronic Properties of Van Der Waals-Epitaxy Films and Interfaces. Physics and Chemistry of Materials With Low-dimensional Structures, 2002, , 317-402.	1.0	20
150	Interfaces of chalcogenide solar cells: a study of the composition at the Cu(In,Ga)Se2/CdS contact. Thin Solid Films, 2005, 480-481, 110-117.	0.8	20
151	Evidence for surface dipole modifications in In2O3-based transparent conductors. Applied Physics Letters, 2008, 92, .	1.5	20
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